

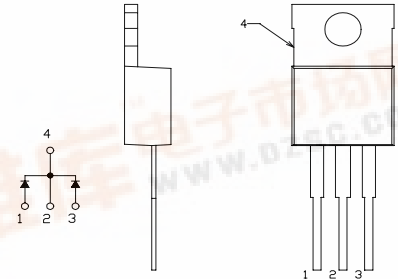


# SBD Type : GCQ10A06

OUTLINE DRAWING

## FEATURES

- \*Similar to TO-220AB Case
- \*Dual Diodes – Cathode Common
- \*Low Forward Voltage Drop
- \*High Surge Capability
- \*Tj=150 °C operation



## Maximum Ratings

Approx Net Weight: 1.9g

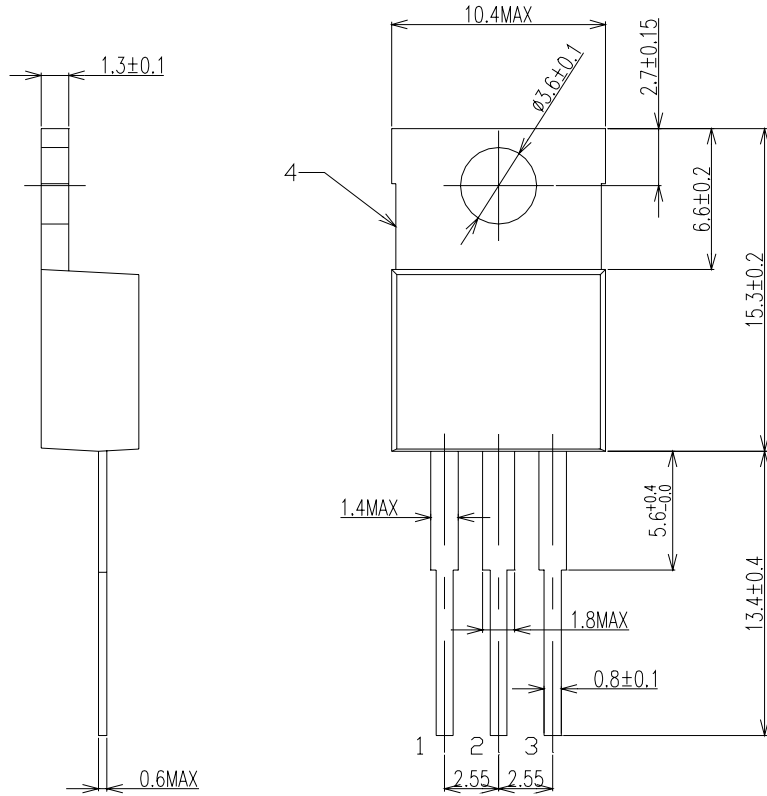
Rating	Symbol	GCQ10A06			Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	60			V
Non-repetitive Peak Reverse Voltage	$V_{RSM}$	65			V
Average Rectified Output Current	$I_O$	10	$T_c=108^{\circ}C$	50 Hz Full Sine Wave Resistive Load	A
RMS Forward Current	$I_{F(RMS)}$	11.1			A
Surge Forward Current	$I_{FSM}$	110	50Hz Full Sine Wave ,1cycle Non-repetitive		A
Operating JunctionTemperature Range	$T_{jw}$	-40 to +150			°C
Storage Temperature Range	$T_{stg}$	-40 to +150			°C
Mounting torque	$F_{tor}$	recommended torque = 0.5			N•m

## Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	$I_{RM}$	$T_j= 25^{\circ}C, V_{RM}= V_{RRM}$ per arm	-	-	5	mA
Peak Forward Voltage	$V_{FM}$	$T_j= 25^{\circ}C, I_{FM}= 5 A$ per arm	-	-	0.58	V
Thermal Resistance	$R_{th(j-c)}$	Junction to Case	-	-	3	°C/W



GCQ10A06 OUTLINE DRAWING (Dimensions in mm)



Center Tap

